## MEC 316 Tutorial Sheet 2 Solutions

1) Each cell generates current current 
$$I_1$$
,  $I_2$   
Total  $I = I_1 + I_2 = I_{d_1} - I_{L_1} + I_{d_2} - I_{L_2}$ 

Voltages across both cells have to be identical for parallel cell configuration, so:

$$I = I_{01} \left[ exp \left( eV/kT \right) - I \right] - I_{L_1} + I_{02} \left[ exp \left( eV/kT \right) - I \right] - I_{L_2}$$

$$= \left( I_{01} + I_{02} \right) \left[ exp \left( eV/kT \right) - I \right] - \left( I_{L_1} + I_{L_2} \right)$$

under open circuit condition, I=0 and exponent term >> 1,

-'. exp (e Voc/kT) = IL

To

Under short circuit, V=0,  $I_{L=}-(I_{L_1}+I_{L_2})=-2.8A$ Need  $I_0$ , and  $I_{02}$ 

-. 
$$V_{0c} \approx \frac{kT}{e} \ln \left( \frac{2.8}{5.66 \times 10^{-11}} \right) = 0.615 \text{ V}$$

Equation for away is: I = 5.66×10 [exp(eV/KT)-1]-2.8

2)  $I = I_0 \left[ \exp(eV/kT) - I \right] - I_L$   $I = \text{current turough resistor} = -\frac{1}{K} = -\frac{0.5}{2} = -0.25 \text{ A}$ substituting and rearronging equation gives:  $I_L = 2\times10^{-10} \left[ \exp(e^{0.5}/kT) - I \right] + 0.25 = 0.347 \text{ A}$ 

Power = V.I. = 0.5 × 0.25 = 0.125W Voc × Isc = 0.532 × 0.347 = 0.184W

Fill factor =  $\frac{\text{Power}}{\text{Voc} \times \text{Isc}} = \frac{0.125}{0.184} = 0.68$ 

This is a reasonable fill factor, so 252 hoad is close to optimum

When the temperature decreases, Io decreases, hence Voc would increase. The minority carrier diffusion length would also increase slightly, so IL would increase. The higher V and larger I will result in more power being developed by the cell.

3) lower = VXI = VIo[exp(eV/KT)-1]-VIL

Maximum in power occurs when 
$$\frac{dP}{dV} = 0$$
 and  $V = V_m$ 

$$\ln\left(\frac{V_{\text{M}}}{0.025}\right)^{-1}\left(\frac{V_{\text{M}}}{0.025}\right) = \ln\left(\frac{50\times10^{3}}{10^{-10}}\right) = 20.03$$

substituting different values for Vm in L.H.S. of above gives 20.89 for Vm = 0.45, so good enough

Lax. Power = Vm x Imax = 19.5 mW

Cell develops maximum power when optimum R(load) is chosen, so  $R = \frac{Vm}{Imex} = 0.45/43.44 \times 10^{-3} = 10.36 SR$ 

Isc × Voc = 0.025 W

4) 
$$V_{0c} = \frac{kT}{e} \ln \left( \frac{I_L}{I_0} + 1 \right)$$
,  $\frac{kT}{e} = 0.025V \text{ at RT}$ ,  $V_{0c} = 0.5V$   
 $I_0 = 2 \times 10^{-10} \text{ A}$ 

substituting into above gives, IL = 97 mA Load current, I = Id-IL = Io[exp(eV/kT)-1]-IL

I at V=0.45V given by  $I=2\times10^{10}$  [exp (0.45/6.025)-1]-0.097=84 mA

Power = VI = 0.45 x 0.084 = 37.8 mW

Efficiency = Pout x 100%

 $Pin = area of ceu \times 1kW$ .  $Eff. = \frac{37.8 \times 10^{-3}}{(25 \times 10^{-3})^2 \times 1000} = 6\%$ 

5) For cells in parallel equations, see Question 1.

First need Io for each cell.

Si cell :  $V_{0c}=0.7 = \frac{kT}{e} \ln \left(\frac{1.4}{I_0}\right) \implies I_0 = 9.68 \times 10^{13} A$ 

FIGATI COLI: Voc = 1.0 = KT lu (1.3) => I. = 5.52 × 10 A

For away under short circuit conditions, V = 0,  $I_{SC} = -1.4 - 1.3 = -2.7A$ 

Under open circuit conditions, I=0 2.7 = 5.52×10<sup>18</sup> [exp(eVoc/kT)-1]+9.68×10<sup>13</sup> [exp(eVoc/kT)-] 2.7 = 9.68×10<sup>13</sup> [exp(eVoc/kT)-1] Voc = 0.716 V

I-V of away is therefore
$$I = \left[9.68 \times 10^{-13} + 5.52 \times 10^{-18}\right] \left[\exp\left(eV/kT\right) - 1\right] - 2.7 \text{ A}$$
Power =  $V \times I$ 

$$V(v)$$
: 0 0.2 0.4 0.55 0.6 0.65 0.7  $I(A)$ : 2.7 2.7 2.7 2.68 2.51 1.3  $P_{ower}(w)$ : 0 0.54 1.08 1.485 1.6.08 1.631 0.91

Maximum power is 
$$\sim 1.631W$$
  
Fill factor = Max. Power =  $\frac{1.631}{0.716 \times 2.7} = 0.84$ 

See Question 3 for first part.

Isc = 100 m A, Io = 
$$10^{-9}$$
 A

(1+eVm) exp(eVm) = 1 + Isc
Io

substitute values for Vm until above is approx. true  $V_{M} = 0.4$  gives L.H.S.  $\approx R.H.S$ .

for max. power, we need max. current,

I max = 10<sup>-9</sup> [exp (0.4/0.025)-1]-0.1A = 91mA

P = Imax × Vmax = 91mA × 0.4 = 36.4mW

Need Voc for fill factor; Voc = KT lu (Isc ) = 0.025 × 18.42

7) For cells in parallel, see Question 1.

Maximum power ~ 143 mW

This occurs at 0.44V when a current of 0.326A flows, so optimum load resistor is:

$$R = \frac{V}{I} = \frac{0.44}{0.326} = 1.35 J2$$

Voc for away = 
$$\frac{KT}{e} ln \left( \frac{I_{L_1} + I_{L_2}}{I_{O_1} + I_{O_2}} \right) = 0.025 ln \left( \frac{0.35}{5.4 \times 10^{-10}} \right)$$
  
= 0.507 V